# **MOSPEC**

#### SILICON NPN POWER TRANSISITORS

... designed for medium-speed switching and amplifier applications

#### **FEATURES**

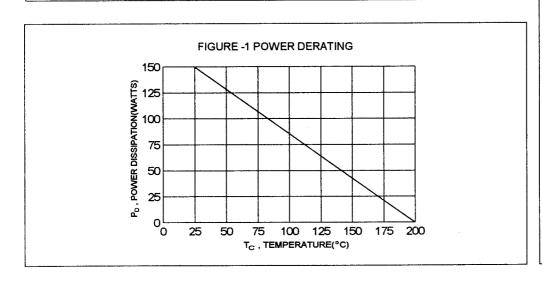
- \* Gain Ranged Specified at 1A and 3A.
- \* Low  $V_{\rm CE(sat)}$ : typically 0.5 V @ I<sub>C</sub>=5 A , I<sub>B</sub>=0.5A \* Excellent Safe Operating Areas
- \* Complementary PNP Types Available 2N3789 thru 2N3792

#### **MAXIMUM RATINGS**

Characteristic	Symbol	2N3713 2N3715	2N3714 2N3716	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80 100		V
Collector-Emitter Voltage	V <sub>CEO</sub>	60 80		V
Emitter-Base Voltage	V <sub>EBO</sub>		V	
Collector Current - Continuous	Ic	1	А	
Base Current-Continuous	l <sub>B</sub>		Α	
Total Power Dissipation @T <sub>c</sub> =25°C Derate above 25°C	P <sub>D</sub>	1! 0.8	W/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-65 to	°C	

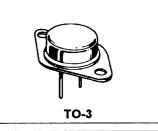
#### THERMAL CHARACTERISTICS

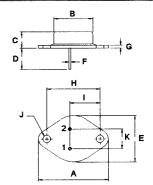
Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	<b>R</b> ⊕ jc	1.17	°C/W



NPN 2N3713 Thru 2N3716

10 AMPERE **POWER TRANSISTORS** NPN SILICON **60-80 VOLTS 150 WATTS** 





PIN 1.BASE 2.EMITTER COLLECTOR(CASE)

DIM	MILLIMETERS			
ואוט	MIN	MAX		
Α	38.75	39.96		
В	19.28	22.23		
С	7.96	9.28		
D	11.18	12.19		
E	25.20	26.67		
F	0.92	1.09		
G	1.38	1.62		
н	29.90	30.40		
1	16.64	17.30		
J	3.88	4.36		
K	10.67	11.18		

## ELECTRICAL CHARACTERISTICS ( T<sub>c</sub> = 25°C unless otherwise noted )

Characteristic		Symbol	Min	Max	Unit		
OFF CHARACTERISTICS							
Collector-Emitter Sustaining Voltage (1) (I <sub>C</sub> = 200 mA, I <sub>B</sub> = 0)	2N3713, 2N3715 2N3714, 2N3716	V <sub>CEO (sus)</sub>	60 80		V		
Collector -Emitter Cutoff Current (V <sub>CE</sub> = 80 V, V <sub>BE(off)</sub> = -1.5V) (V <sub>CE</sub> = 100 V, V <sub>BE(off)</sub> = -1.5V) (V <sub>CE</sub> = 60 V, V <sub>BE(off)</sub> = -1.5V,T <sub>C</sub> = 150°C) (V <sub>CE</sub> = 80 V, V <sub>BE(off)</sub> = -1.5V,T <sub>C</sub> = 150°C)	2N3713, 2N3715 2N3714, 2N3716 2N3713, 2N3715 2N3714, 2N3716	I <sub>CEX</sub>		1.0 1.0 10	mA		
Emitter Cutoff Current (V <sub>EB</sub> = 7.0 V, I <sub>C</sub> =0 )	All Types	I <sub>EBO</sub>		5.0	mA		

### **ON CHARACTERISTICS (1)**

DC Current Gain		hFE			
( I <sub>C</sub> = 1.0 A, V <sub>CE</sub> = 2.0 V )	2N3713, 2N3714		25	90	
32	2N3715, 2N3716		50	180	
(I <sub>C</sub> = 3.0 A, V <sub>CE</sub> = 2.0 V)	2N3713, 2N3714		15		
	2N3715, 2N3716		30		
Collector-Emitter Saturation Voltage		V <sub>CE(sat)</sub>			V
(I <sub>C</sub> = 5.0 A, I <sub>R</sub> = 0.5 A)	2N3713, 2N3714	CE(Sat)		1.0	
	2N3715, 2N3716			0.8	
Base-Emitter Saturation Voltage		V <sub>BE(sat)</sub>			V
( l <sub>c</sub> = 5.0 A, l <sub>R</sub> = 0.5 A )	2N3713, 2N3714	DE(Sat)		2.0	
	2N3715, 2N3716			1.5	
Base-Emitter On Voltage		V <sub>BE(on)</sub>			V
( l <sub>c</sub> = 3.0 A, V <sub>cE</sub> = 2.0 V )	All Types	BE(OII)		1.5	

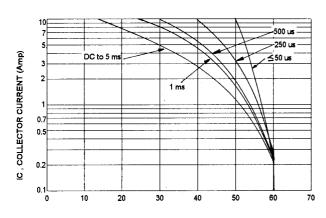
#### **DYNAMIC CHARACTERISTICS**

Current-Gain Bandwidth Product	f <sub>T</sub>		MHz
(I <sub>C</sub> = 500 mA,V <sub>CE</sub> = 10 V, f = 1MHz)	•	4.0	

<sup>(1)</sup> Pulse Test: Pulse width = 300 us , Duty Cycle  $\leq 2.0\%$  (2)  $f_{_T}=~\left|h_{f\,e}\right| \circ f_{_{test}}$ 

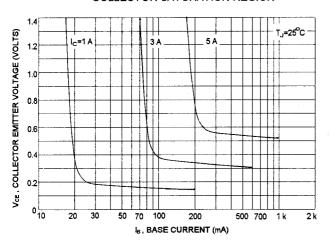
#### 2N3713,2N3715

#### **ACTIVE REGION SAFE OPERATING AREA**

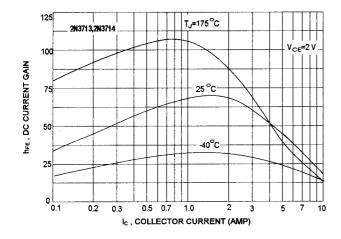


VCE, COLLECTOR EMITTER VOLTAGE (VOLTS)

#### **COLLECTOR SATURATION REGION**

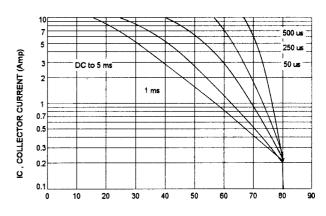


DC CURRENT GAIN



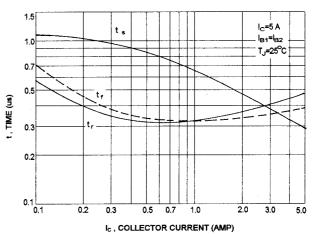
#### 2N3714,2N3716

#### **ACTIVE REGION SAFE OPERATING AREA**

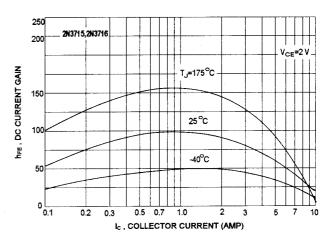


VCE , COLLECTOR EMITTER VOLTAGE (VOLTS)

#### TYPICAL SWITCHING TIME



#### DC CURRENT GAIN



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